

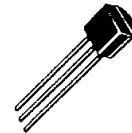
# NPN Silicon High Frequency Transistors

... designed for low noise, wide dynamic range front-end amplifiers and low-noise VCO's. Available in two surface-mountable plastic package styles, as well as the popular TO-92 package. This Motorola series of small-signal plastic transistors offers superior quality and performance at low cost.

- High Gain-Bandwidth Product  
 $f_T = 8 \text{ GHz (Typ) } @ 50 \text{ mA}$
- Low Noise Figure  
 $NF = 2 \text{ dB (Typ) } @ 500 \text{ MHz}$
- High Gain  
 $GNF = 17 \text{ dB (Typ) } @ 30 \text{ mA/500 MHz}$
- State-of-the-Art Technology  
 Fine Line Geometry  
 Ion-Implanted Arsenic Emitters  
 Gold Top Metallization and Wires  
 Silicon Nitride Passivation
- Tape and Reel Packaging Options
- MMBR571 Available in Low Profile, Add L Suffix

**MPS571  
 MXR571  
 MMBR571**

**LOW NOISE  
 HIGH RF GAIN**



**TO-92  
 CASE 29  
 MPS571**



**SOT-89  
 CASE 345  
 MXR571**



**SOT-23  
 CASE 318  
 MMBR571  
 Standard and Low Profile**

## MAXIMUM RATINGS

Ratings	Symbol	MPS571	MXR571	MMBR571	Unit
Collector-Emitter Voltage	$V_{CEO}$	10			Vdc
Collector-Base Voltage	$V_{CBO}$	20			Vdc
Emitter-Base Voltage	$V_{EBO}$	3			Vdc
Collector Current — Continuous	$I_C$	80			mA
Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	625	400 (Free Air)	200 (Free Air)	mW
Storage Temperature	$T_{stg}$	-55 to +150			$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage ( $I_C = 0.1\text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CEO}$	10	12	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 1\text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 50\ \mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	2.5	—	—	Vdc
Collector Cutoff Current ( $V_{CB} = 8\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	—	—	10	$\mu\text{Adc}$

**ON CHARACTERISTICS**

DC Current Gain ( $I_C = 30\text{ mAdc}$ , $V_{CE} = 5\text{ Vdc}$ )	$h_{FE}$	50	—	300	—
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**DYNAMIC CHARACTERISTICS**

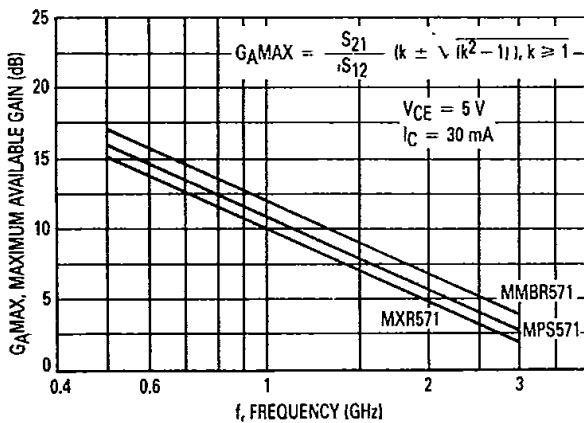
Collector-Base Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1\text{ MHz}$ )	$C_{cb}$	—	0.7	1	pF
Current Gain-Bandwidth Product ( $V_{CE} = 5\text{ Vdc}$ , $I_C = 50\text{ mAdc}$ , $f = 1\text{ GHz}$ )	$f_T$	—	6	—	GHz
		MPS571	7	—	
		MXR571	8	—	
		MMBR571	—	—	

**FUNCTIONAL TESTS**

Gain $\alpha$ Noise Figure ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5\text{ Vdc}$ )		$G_{NF}$	—	14	—	dB
	MPS571 $f = 0.5\text{ GHz}$		—	9	—	
	MPS571 $f = 1\text{ GHz}$		—	15	—	
	MXR571 $f = 0.5\text{ GHz}$		—	9.5	—	
	MXR571 $f = 1\text{ GHz}$		—	16.5	—	
	MMBR571 $f = 0.5\text{ GHz}$		—	10.5	—	
	MMBR571 $f = 1\text{ GHz}$		—	—	—	
Noise Figure ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5\text{ Vdc}$ )		NF	—	2	—	dB
	MPS571 $f = 0.5\text{ GHz}$		—	2.6	—	
	MPS571 $f = 1\text{ GHz}$		—	2.1	—	
	MXR571 $f = 0.5\text{ GHz}$		—	2.7	—	
	MXR571 $f = 1\text{ GHz}$		—	2	—	
	MMBR571 $f = 0.5\text{ GHz}$		—	2.6	—	
	MMBR571 $f = 1\text{ GHz}$		—	—	—	

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**Figure 1. Maximum Available Gain versus Frequency**



**Figure 2. Current Gain-Bandwidth versus Collector Current @ 1 GHz**

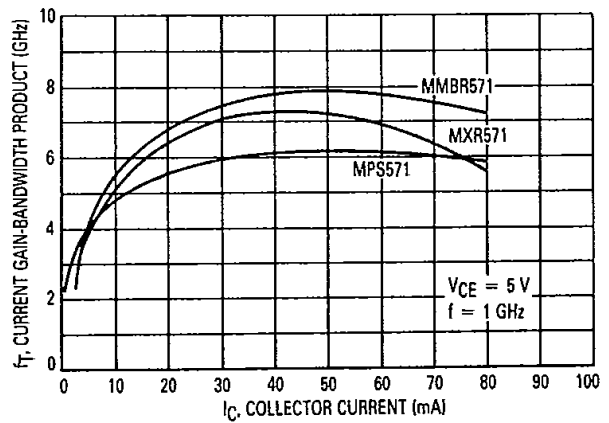


Figure 3. Input Capacitance versus Emitter Base Voltage

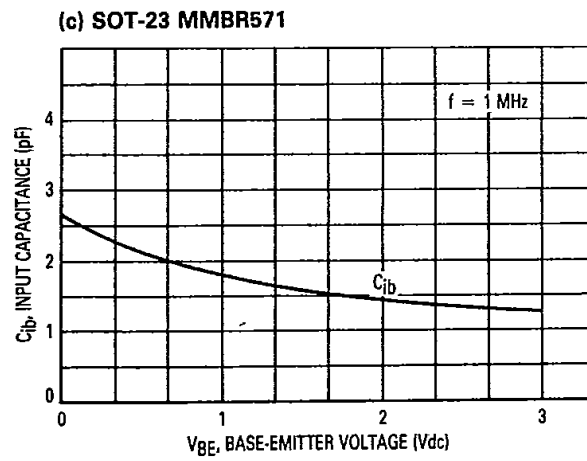
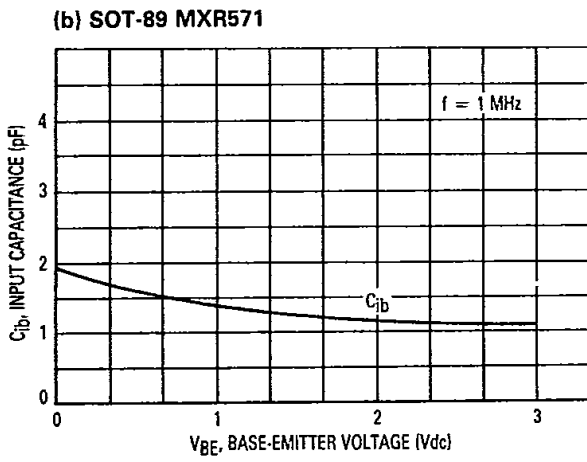
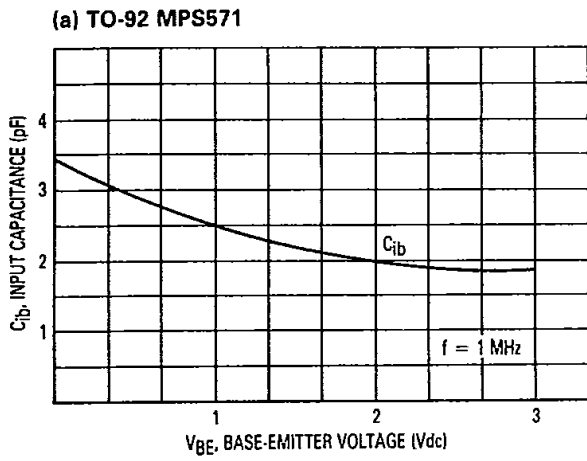


Figure 4. Output Capacitances versus Collector-Base Voltage

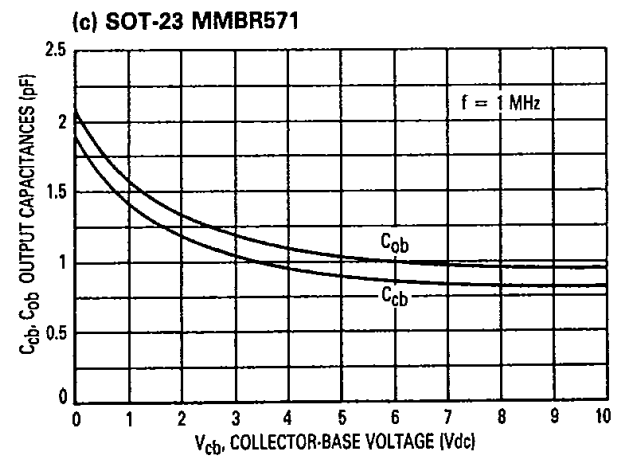
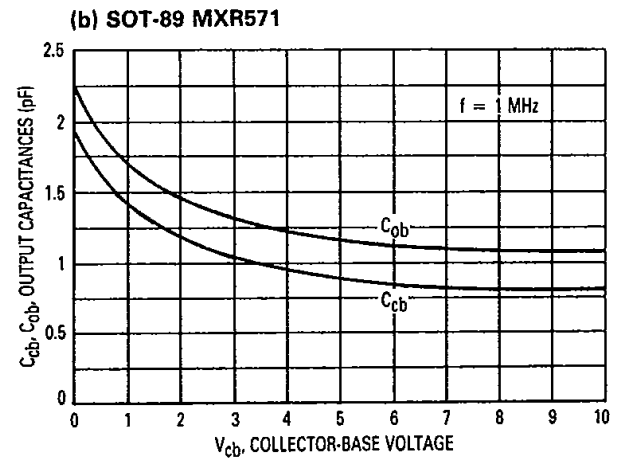
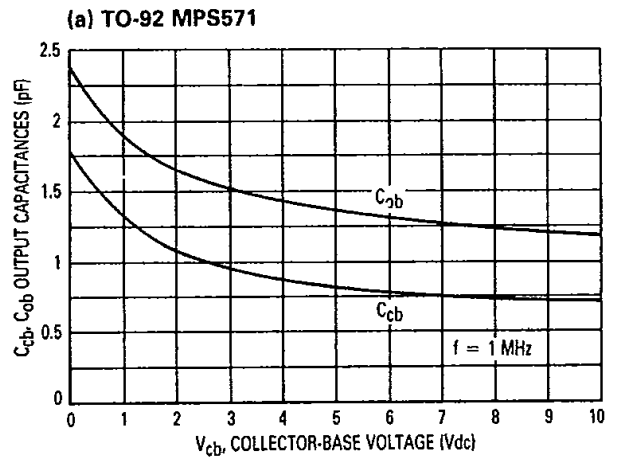


Figure 5. Gain at Noise Figure versus Collector Current

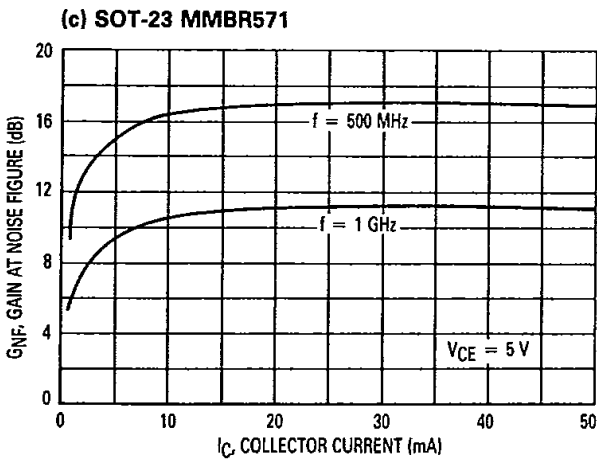
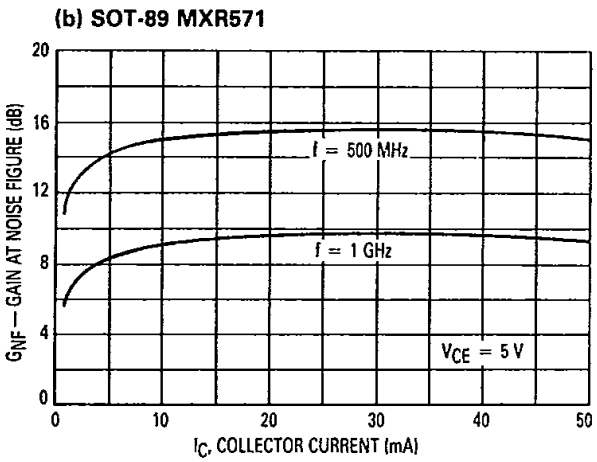
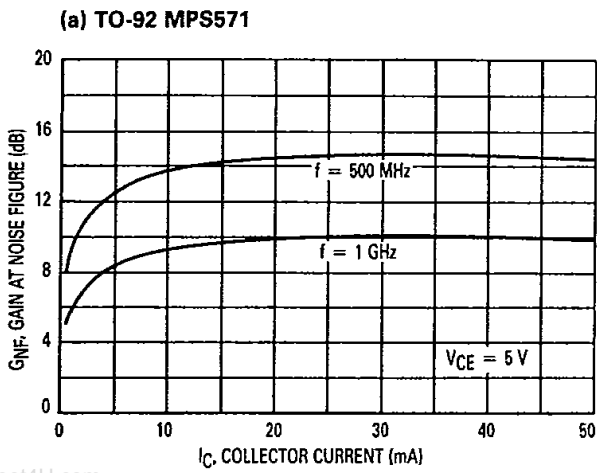


Figure 6. Noise Figure versus Collector Current

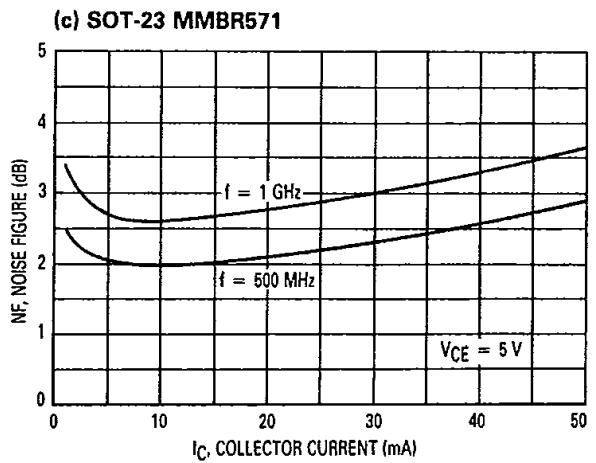
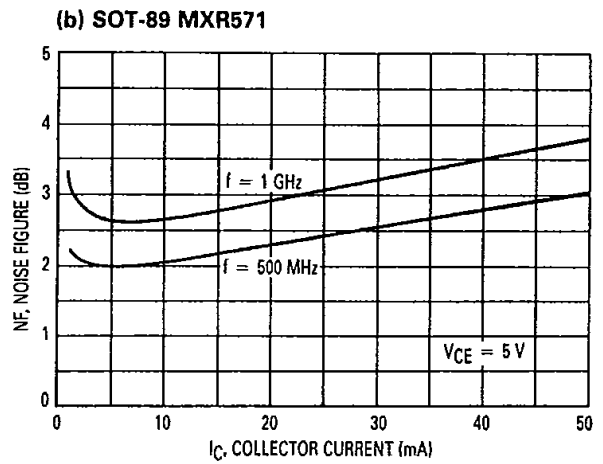
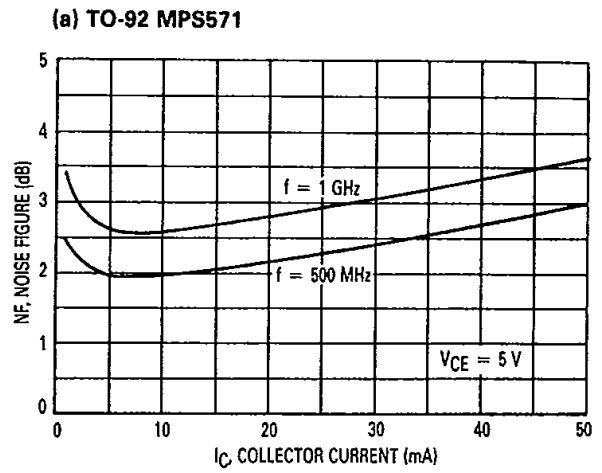


Figure 7. Gain at Noise Figure and Noise Figure versus Frequency

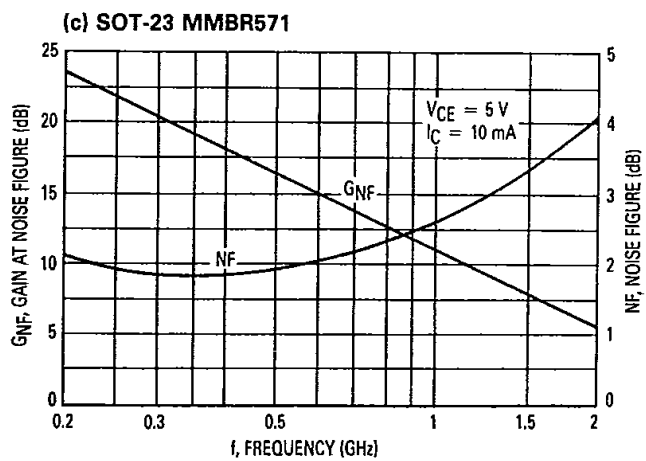
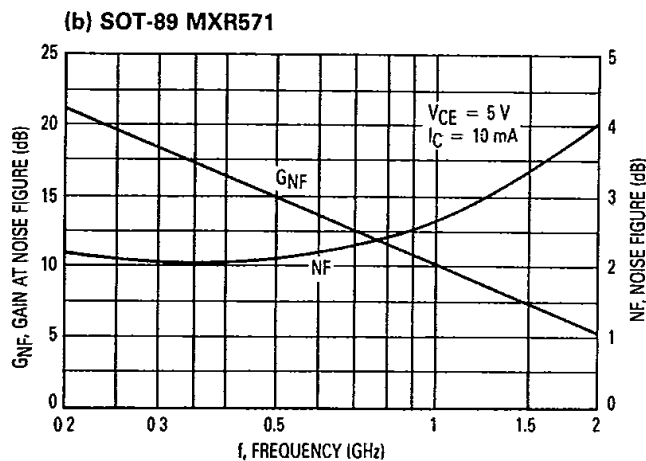
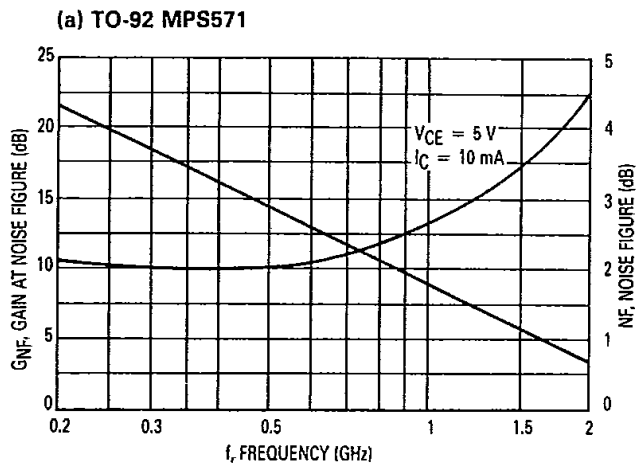
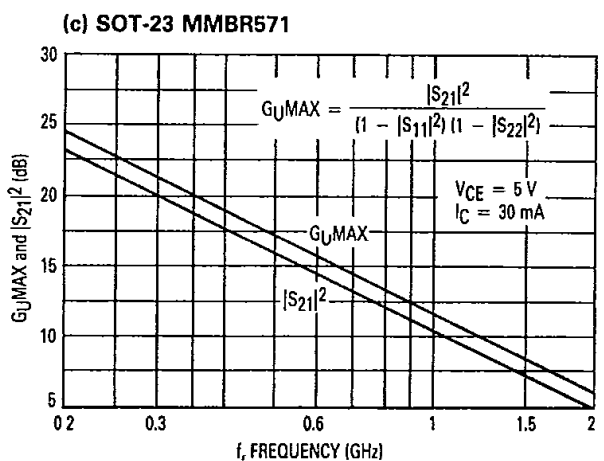
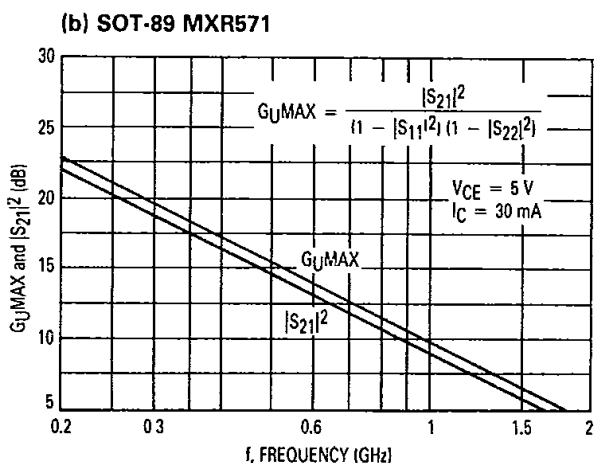
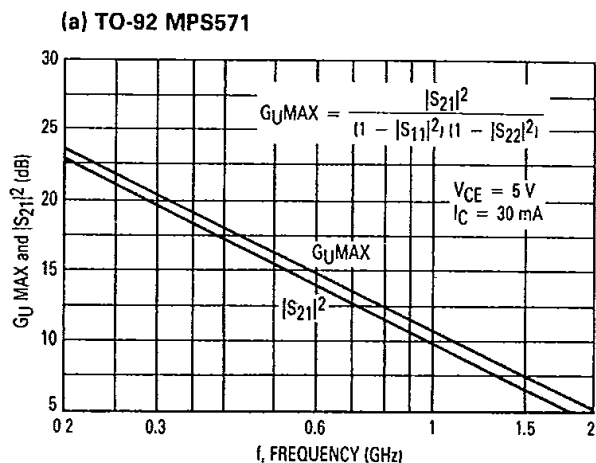
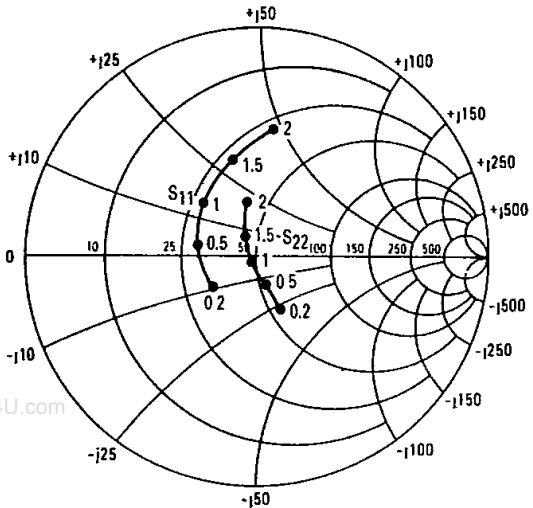


Figure 8. Maximum Unilateral Gain and Insertion Gain versus Frequency

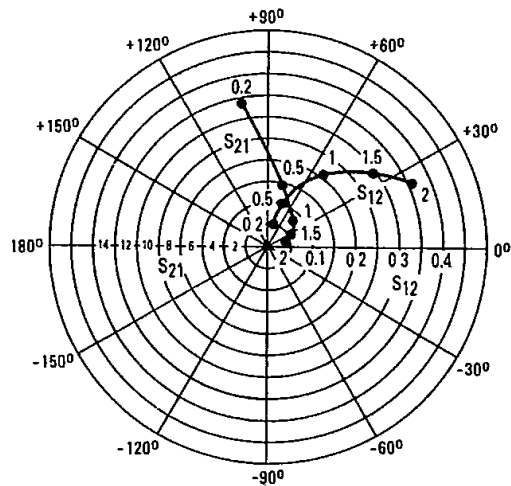


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**INPUT/OUTPUT REFLECTION COEFFICIENTS**  
 versus FREQUENCY  
 $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}$



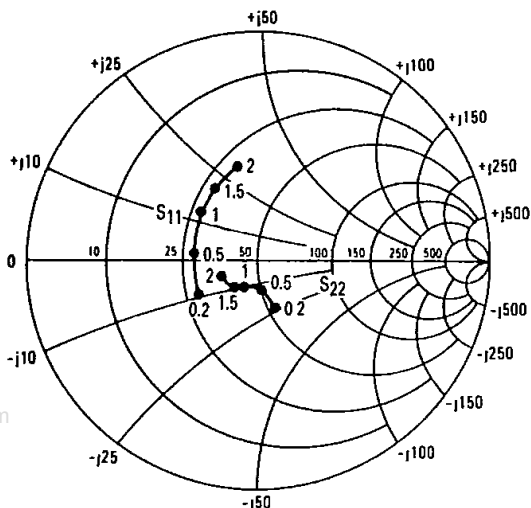
**FORWARD/REVERSE TRANSMISSION COEFFICIENTS**  
 versus FREQUENCY  
 $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}$



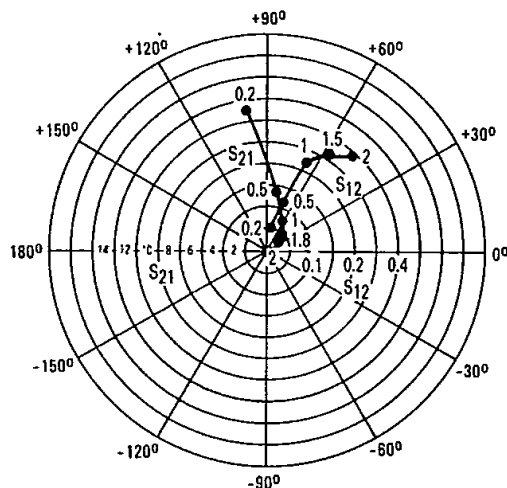
**COMMON EMITTER S-PARAMETERS**

V <sub>CE</sub> (Volts)	I <sub>C</sub> (mA)	f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
			S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
5	5	200	0.62	-80	8.22	122	0.07	56	0.63	-44
		500	0.40	-148	4.52	87	0.11	50	0.36	-58
		1000	0.39	155	2.51	54	0.16	48	0.23	-78
		1500	0.46	122	1.86	32	0.23	42	0.15	-114
		2000	0.59	100	1.50	14	0.31	33	0.14	173
15	15	200	0.33	-121	12.88	105	0.05	67	0.37	-59
		500	0.28	-175	5.62	79	0.10	65	0.18	-67
		1000	0.32	143	2.99	53	0.19	55	0.08	-94
		1500	0.40	117	2.14	32	0.27	42	0.07	171
		2000	0.55	95	1.74	17	0.35	30	0.198	117
30	30	200	0.23	-143	13.65	99	0.05	75	0.26	-62
		500	0.23	169	5.75	76	0.11	70	0.13	-68
		1000	0.30	130	3.05	50	0.21	55	0.04	-136
		1500	0.41	106	2.11	28	0.29	38	0.12	130
		2000	0.56	85	1.70	11	0.36	23	0.26	102
50	50	200	0.21	-158	13.96	96	0.05	79	0.21	-61
		500	0.23	162	5.82	75	0.11	72	0.11	-66
		1000	0.30	128	3.09	49	0.21	56	0.03	-149
		1500	0.41	105	2.11	28	0.29	39	0.12	127
		2000	0.56	84	1.70	11	0.36	23	0.27	100

**INPUT/OUTPUT REFLECTION COEFFICIENTS  
versus FREQUENCY**  
VCE = 5 V, IC = 30 mA



**FORWARD/REVERSE TRANSMISSION  
COEFFICIENTS versus FREQUENCY**  
VCE = 5 V, IC = 30 mA



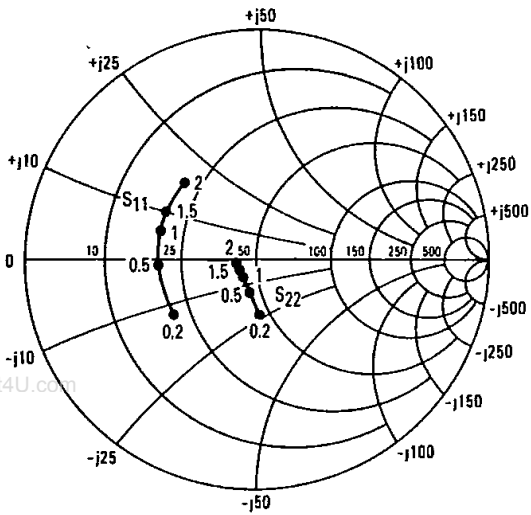
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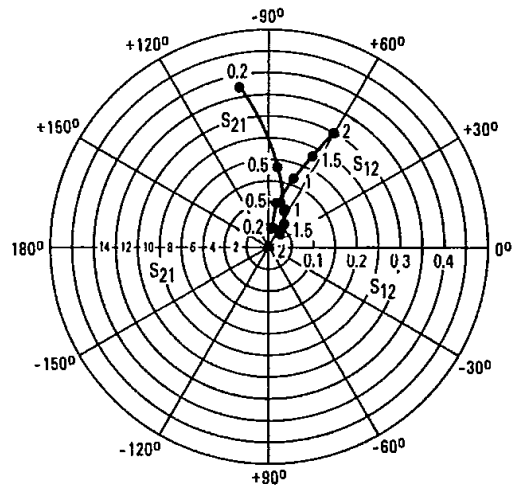
**COMMON EMITTER S-PARAMETERS**

VCE (Volts)	IC (mA)	f (MHz)	S11		S21		S12		S22	
			S11	∠φ	S21	∠φ	S12	∠φ	S22	∠φ
5	5	200	0.60	-84	7.94	120	0.08	56	0.58	-45
		500	0.39	-152	4.17	86	0.11	54	0.34	-56
		1000	0.39	161	2.32	62	0.19	58	0.27	-71
		1500	0.44	132	1.64	45	0.26	55	0.25	-90
		2000	0.49	106	1.33	31	0.32	52	0.26	-106
	15	200	0.33	-126	11.89	101	0.06	67	0.32	-63
		500	0.29	-178	5.13	81	0.11	69	0.18	-73
		1000	0.33	148	2.75	62	0.22	65	0.15	-99
		1500	0.37	123	1.93	47	0.30	56	0.16	-118
		2000	0.42	100	1.55	34	0.37	49	0.17	-139
	30	200	0.28	-149	12.74	97	0.05	74	0.23	-69
		500	0.27	174	5.37	79	0.11	73	0.13	-82
		1000	0.32	144	2.85	62	0.22	66	0.13	-112
		1500	0.36	120	2.02	47	0.31	57	0.15	-132
		2000	0.40	98	1.62	35	0.38	49	0.17	-152
	50	200	0.26	-162	13.03	94	0.05	77	0.18	-71
		500	0.27	169	5.43	79	0.12	75	0.11	-85
		1000	0.32	142	2.88	62	0.22	67	0.12	-117
		1500	0.36	119	2.02	47	0.31	57	0.15	-137
		2000	0.40	97	1.60	35	0.38	49	0.17	-155

**INPUT/OUTPUT REFLECTION COEFFICIENTS**  
 versus FREQUENCY  
 $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}$



**FORWARD/REVERSE TRANSMISSION COEFFICIENTS**  
 versus FREQUENCY  
 $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}$



**COMMON EMITTER S-PARAMETERS**

V <sub>CE</sub> (Volts)	I <sub>C</sub> (mA)	f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
			S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
5	5	200	0.68	-82	8.41	126	0.07	53	0.61	-45
		500	0.52	-142	4.62	93	0.10	46	0.35	-60
		1000	0.50	179	2.57	72	0.14	53	0.26	-71
		1500	0.51	161	1.82	57	0.19	58	0.24	-77
		2000	0.52	143	1.48	45	0.24	59	0.22	-86
	15	200	0.46	-125	13.65	108	0.05	60	0.35	-73
		500	0.43	-169	6.03	86	0.09	66	0.17	-94
		1000	0.44	168	3.20	72	0.16	67	0.14	-111
		1500	0.45	152	2.21	58	0.22	64	0.11	-118
		2000	0.46	137	1.80	48	0.29	59	0.10	-131
	30	200	0.42	-148	14.79	102	0.04	68	0.26	-87
		500	0.41	-177	6.31	84	0.09	72	0.14	-115
		1000	0.42	165	3.35	71	0.16	70	0.12	-135
		1500	0.44	151	2.29	59	0.23	65	0.11	-144
		2000	0.44	135	1.84	48	0.30	60	0.10	-157
	50	200	0.41	-159	15.14	98	0.04	73	0.21	-96
		500	0.42	179	6.38	83	0.09	75	0.13	-124
		1000	0.43	163	3.35	70	0.16	71	0.12	-143
		1500	0.44	148	2.32	58	0.23	66	0.10	-151
		2000	0.45	134	1.84	48	0.30	60	0.09	-163



OUTLINE DIMENSIONS

**SOT-23  
CASE 318-02  
TO-236AA  
Standard**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.80	3.04	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	0.85	1.20	0.033	0.0472
D	0.37	0.46	0.0150	0.0177
F	0.065	0.130	0.0026	0.0051
G	1.78	2.04	0.0701	0.0807
H	0.51	0.60	0.0200	0.0236
K	0.10	0.25	0.0040	0.0098
L	2.10	2.50	0.0830	0.0984
M	0.45	0.60	0.0180	0.0236
N	0.63	1.02	0.0250	0.0401

STYLE 6  
PIN 1 BASE  
2. EMITTER  
3. COLLECTOR

NOTES  
1. DIMENSIONING AND TOLERANCING PER ANSI  
2. Y14.5M, 1982.  
CONTROLLING DIMENSION: MILLIMETERS

**SOT-23  
CASE 318-03  
TO-236AB  
Low Profile**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.60	3.04	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	0.89	1.11	0.035	0.044
D	0.37	0.46	0.015	0.0177
F	0.065	0.130	0.0026	0.0051
G	1.78	2.04	0.0701	0.0807
H	0.51	0.60	0.0200	0.0236
K	0.013	0.100	0.0005	0.0040
L	2.10	2.50	0.0830	0.0984
M	0.45	0.60	0.018	0.0236
N	0.89	1.02	0.0350	0.0401

STYLE 6  
PIN 1 BASE  
2. EMITTER  
3. COLLECTOR

NOTES  
1. DIMENSIONING AND TOLERANCING PER ANSI  
2. Y14.5M, 1982.  
CONTROLLING DIMENSION: MILLIMETERS

**TO-92  
CASE 29-02  
TO-226AA  
PLASTIC**

NOTES  
1. CONTOUR OF PACKAGE BEYOND ZONE "P" IS UNCONTROLLED.  
2. DIM "F" APPLIES BETWEEN "H" AND "L". DIM "D" & "S" APPLIES BETWEEN "L" & 12.70 mm (0.5") FROM SEATING PLANE. LEAD DIM IS UNCONTROLLED IN "H" & BEYOND 12.70 mm (0.5") FROM SEATING PLANE

STYLE 2  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	5.33	0.170	0.210
B	4.44	5.21	0.175	0.205
C	3.18	4.19	0.125	0.165
D	0.41	0.56	0.016	0.022
F	0.41	0.48	0.016	0.019
G	1.14	1.40	0.045	0.055
H	—	2.54	—	0.100
J	2.41	2.67	0.095	0.105
K	12.70	—	0.500	—
L	6.35	—	0.250	—
N	2.03	2.67	0.080	0.105
P	2.92	—	0.115	—
R	3.43	—	0.135	—
S	0.36	0.41	0.014	0.016

**SOT-89  
CASE 345-01  
PLASTIC**

STYLE 1  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER

NOTES  
1. DIMENSIONS A AND B ARE DATUMS.  
2. -T- IS SEATING PLANE.  
3. POSITIONAL TOLERANCE FOR LEADS  
Ⓜ 0.10 (0.004) Ⓜ I B S A S  
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973  
5. CONTROLLING DIM. MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.40	4.60	0.174	0.181
B	2.29	2.60	0.091	0.102
C	1.40	1.60	0.056	0.062
D	0.36	0.48	0.015	0.018
E	1.62	1.80	0.064	0.070
F	0.44	0.53	0.018	0.020
G	1.50 BSC	—	0.059 BSC	—
J	0.35	0.44	0.014	0.017
K	0.80	1.04	0.032	0.040
L	3.00 BSC	—	0.118 BSC	—
N	2.04	2.28	0.081	0.089
P	3.94	4.25	0.156	0.167